onsemi

Dual Series High Voltage Switching Diode

MMBD1401ALT1G, MMBD1403ALT1G

Features

- Moisture Sensitivity Level: 1
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V _R	250	V
Repetitive Peak Reverse Voltage	V _{RRM}	250	V
Peak Forward Current	١ _F	225	mA
DC Forward Current	١ _F	600	mA
Recurrent Peak Forward Current	l _f	700	mA
Peak Forward Surge Current	I _{FM(surge)}	625	mA

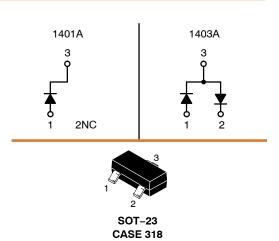
THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$	P _D	225	mW
Derate above 25°C		1.8	mW/∘C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) $T_{\Delta} = 25^{\circ}C$	P _D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	−55 to +150	°C

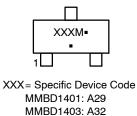
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR–5 = 1.0 \times 0.75 \times 0.062 in.

2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.



MARKING DIAGRAM



M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBD1401ALT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBD1403ALT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

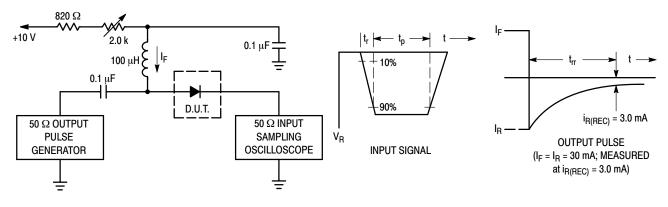
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBD1401ALT1G, MMBD1403ALT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Voltage Leakage Current (V _R = 200 Vdc) (V _R = 175 Vdc)	I _R		40 100	nA
Reverse Breakdown Voltage (I _{BR} = 100 μAdc)	V _(BR)	250	-	V
Forward Voltage (I _F = 10 mA) (I _F = 50 mA) (I _F = 200 mA) (I _F = 300 mA)	V _F	- 760 - -	800 920 1.1 1.25	mV mV V V
Diode Capacitance (V _R = 0, f = 1.0 MHz)	CD	-	5.0	pF
Reverse Recovery Time (I _F = I _R = 30 mA, I _{RR} = 1.0 mA, R _L = 100 Ω)	t _{rr}	-	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



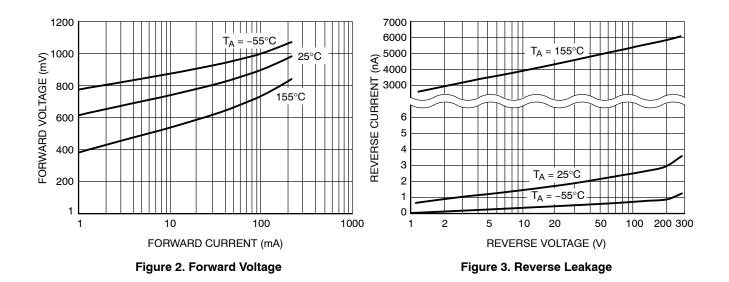
Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 30 mA. 2. Input pulse is adjusted so I_{R(peak)} is equal to 30 mA.

3. t_p » t_{rr}

Figure 1. Recovery Time Equivalent Test Circuit

MMBD1401ALT1G, MMBD1403ALT1G

TYPICAL CHARACTERISTICS



MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

D

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TOP VIEW

SIDE VIEW

Нe

DETAIL A

-3X b

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SCALE 4:1

A____ ' A1SOT-23 (TO-236) CASE 318 ISSUE AT

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DETAIL A

END VIEW

DATE 01 MAR 2023

NDTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIM	IETERS		INCHES		
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*



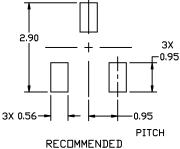


XXX = Specific Device Code

M = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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